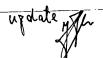
	***	Search Text	DB	Time stamp 2002/06/03 08:43
Number	Hits	TOTAL COLC \ OF	USPAT;	2002/06/03 08:43
	65	(("257/213").CCLS.) or (("257/327").CCLS.)	US-PGPUB;	ļ
		or (("257/335").CCLS.) or	EPO; JPO;	
		//#257/239"\ CCLS.) Or	DERWENT; !	
		(("257/355").CCLS.)) and transistor and	IBM_TDB	
		11-tion add mode	i :	
		("dmos.ti,ab. and buried.ti,ab. and	USPAT;	2002/06/02 18:26
	0	depletion.ti,ab.").PN.	US-PGPUB;	
		depietion.ci,ab. /.im	EPO; JPO;	
	l l		DERWENT;	
	1		IBM_TDB	
		dmos.ti,ab. and buried.ti,ab. and	USPAT;	2002/01/06 15:09
	3	depletion.ti,ab.	US-PGPUB;	
		depietion.ci,ab.	EPO; JPO;	
	'		DERWENT;	
			IBM_TDB	
		jp-02122672\$-\$.did.	USPAT;	2002/01/06 15:02
•	2	Jp-021226725-3.did.	US-PGPUB;	
			EPO; JPO;	Į.
			DERWENT;	
			IBM_TDB	
	_	002216069-5 did	USPAT;	2002/01/06 15:02
	2	jp-08321606\$-\$.did.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	!
			IBM TDB	
		, and buried ti ab	USPAT;	2002/01/06 15:09
-	78	dmos.ti,ab. and buried.ti,ab.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
		, , , , , , , , , , , , , , , , , , , ,	USPAT	2002/01/06 15:11
_	19	dmos.ti,ab. and buried.ti,ab.	USPAT	2002/01/06 15:12
_	0	dmos.ti,ab. and buried.ti,ab. and	001111	
		withstand adj2 voltage.ti,ab.	USPAT	2002/01/06 15:29
_	1	dmos.ti.ab. and buried.ti.ab. and	001711	
		withstand adj2 voltage	USPAT;	2002/01/06 15:31
_	500		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
			USPAT;	2002/06/02 18:3
_	13	((("257/213").CCLS.) or		2002, 03, 02
		(("257/288").CCLS.) or (("25//32/").CCLS.)	EPO; JPO;	
		or (("257/335").CCLS.) or	DERWENT;	
		1 (1"257/339") CCLS.) or	IBM TDB	
		(("257/355").CCLS.)) and buried.cim. and	TEM-TOD	
		(dmos or dmosfet).ti,ab.	USPAT;	2002/01/06 15:3
_	74	(1 2002, 02, 00
		(("257/288").CCLS.) or (("25//32/").CCLS.)		
		or (("257/335").CCLS.) or	ELO, 910,	
		1/1"257/339") CCLS.) or	DERWENT;	
		//"257/355") CCLS.)) and burled.Cim. and	IBM_TDB	
		/dmos or dmosfet or fet or fleid adj	İ	
		-ffort add transistor or mos or mosiet or		
		nmso or nmosfet or pmos or pmosfet).ti,ab	•	2002/01/06 17-5
	7.	e ///#257/213") CCLS.) or	OSEAL	2002/01/06 17:5
-	/	(("257/288").CCLS.) or (("257/327").CCLS.) US-PGPUB;	
		or (("257/335").CCLS.) or	EFO, OLO,	
		//#257/220"\ CCT.S \ OT	DERWENT;	
		(///257/355") CCLS.)) and buried.clm. and	IBM_TDB	
		/dmag or dmosfet or fet or Ileia au	_	
		effect adj transistor or mos or mosfet or		
		nmos or nmosfet or pmos or pmosfet).ti,ab	.	
		nmos or nmostet of phios of phioster, erras	USPAT;	2002/01/06 18:1
-		1 5742087.pn. and depletion	US-PGPUB;	
			EPO; JPO;	i
			DERWENT;	
			IBM TDB	
		1	I I DM TOTAL	1



				10.6 10 10
_	72	(first adj buried and second adj	USPAT;	2002/01/06 18:13
		buried).clm. and (breakdown adj voltage or	US-PGPUB;	
		withstand adj voltage)	EPO; JPO;	
			DERWENT; IBM TDB	
			USPAT;	2002/01/06 18:27
-	18	(first adj buried and second adj	US-PGPUB;	2002/01/00
		buried).clm. and (breakdown adj voltage or withstand adj voltage) and impurity and	EPO; JPO;	
	[DERWENT;	
		switching	IBM TDB	
	122	(first adj buried and second adj buried)	USPAT;	2002/01/07 10:32
_	122	and (breakdown adj voltage or withstand	US-PGPUB;	
		adj voltage)	EPO; JPO;	ĺ
		adj vozedge,	DERWENT;	
			IBM_TDB	
_	987	switching near10 diode and 257/\$6.ccls.	USPAT;	2002/01/06 20:09
			US-PGPUB;	
	Į		EPO; JPO;	
			DERWENT;	
		057/05	IBM_TDB	2002/01/06 20:09
-	987	(switching near10 diode) and 257/\$6.ccls.	USPAT; US-PGPUB;	2002/01/00 20:03
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
		(switching adj2 diode) and 257/\$6.ccls.	USPAT;	2002/01/06 20:09
-	203	(switching adj2 diode) and 237740.ccis.	US-PGPUB;	2002, 12, 11
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	38	(switching adj2 diode).ti,ab. and	USPAT;	2002/01/06 20:21
-	30	257/\$6.ccls.	US-PGPUB;	
		2317 40.0010.	EPO; JPO;	ļ
			DERWENT;	
			IBM_TDB	2222 (21 (26 22 22
-	0		USPAT;	2002/01/06 20:22
		257/\$6.ccls. and galbiati.in.	US-PGPUB;	
·			EPO; JPO;	1
			DERWENT; IBM TDB	
		l l l l l l l l l l l l l l l l l l l	USPAT;	2002/01/06 20:23
-	0		US-PGPUB;	2002/01/00 20120
		257/\$6.ccls. and ludikhuize.in.	EPO; JPO;	
			DERWENT;	
İ			IBM TDB	
	(1	fifth adj impurity.clm. and 257/\$6.ccls.	USPAT;	2002/01/07 08:16
-	ρ1	Titth adj impulity.cim. and 251740.00201	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	18	(fifth adj impurity.clm. and 257/\$6.ccls.)	USPAT;	2002/01/07 08:17
		and switching	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/01/07 10-54
-	43	(first adj impurity near12 second adj	USPAT;	2002/01/07 10:54
		impurity) near12 surround\$3	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
		de la la la la la la la la la la la la la	USPAT;	2002/01/07 11:42
-	6	((first adj impurity near12 second adj		1
		impurity) near12 surround\$3) and switching	EPO; JPO;	1
			DERWENT;	į
			IBM TDB	
	12	(buried adj region near10 gap) and	USPAT;	2002/01/07 11:43
-	12	(257/\$6.ccls. or 438/\$6.ccls.)	US-PGPUB;	
		(201740.0020. 02 100710.00207	EPO; JPO;	
			DERWENT;	

			USPAT;	2002/01/07 14:28
-	3	5874767.pn.	USPAT; US-PGPUB;	2002/01/07 14.20
			EPO; JPO;	
			DERWENT;	!
			IBM_TDB	0000 (01 (07 14 21
-	298	((slit or gap or opening) near10 buried)	USPAT;	2002/01/07 14:31
		and (withstand or breakdown) adj voltage	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	273	((slit or gap or opening) near10 buried)	USPĀT;	2002/01/07 14:33
}		and (withstand or breakdown) adj voltage	US-PGPUB;	
		and (438/\$6.ccls. or 257/\$6.ccls.)	EPO; JPO;	
			DERWENT;	
	52	((slit or gap) near10 buried) and	IBM_TDB USPAT;	2002/01/07 14:40
_	52	(withstand or breakdown) adj voltage and	US-PGPUB;	2002,01,01
		(438/\$6.ccls. or 257/\$6.ccls.)	EPO; JPO;	
		(100) + 0.0025. 02 20.0 1.112.	DERWENT;	
			IBM_TDB	
_	14	((slit or gap) near10 buried adj2 (region	USPAT;	2002/01/07 14:45
		or layer)) and (withstand or breakdown)	US-PGPUB; EPO; JPO;	
		adj voltage and (438/\$6.ccls. or 257/\$6.ccls.)	DERWENT;	
		25//\$6.CC1S.)	IBM TDB	
_	14	((slit or gap) near10 buried adj2	USPAT;	2002/01/07 15:32
		("regions" or "layers")) and (withstand or	US-PGPUB;	
		breakdown) adj voltage and (438/\$6.ccls.	EPO; JPO;	
		or 257/\$6.ccls.)	DERWENT;	
			IBM_TDB	: ! 2002/01/07 15:32
-	382	(257/653).CCLS.	USPAT; US-PGPUB;	2002/01/07 13.32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	101	(257/654).CCLS.	USPĀT;	2002/01/07 15:32
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
	7	((("257/653").CCLS.) or	USPAT;	2002/01/07 15:33
_	/	((("257/654").CCLS.)) and buried and (slit	US-PGPUB;	
		or gap)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/01/07 17:19
-	472	(("257/653").CCLS.) or (("257/654").CCLS.)	USPAT; US-PGPUB;	2002/01/07 17:19
			EPO; JPO;	
	1		DERWENT;	
			IBM TDB	
-	220		USPAT;	2002/01/07 16:26
		(recess\$3 or indent\$5 or gap)	US-PGPUB;	•
			EPO; JPO; DERWENT;	
			IBM TDB	
	70	buried adj2 ("regions" or "layers") near12	USPAT;	2002/01/07 16:26
_	/0	(recess\$3 or indent\$5 or gap)	US-PGPUB;	
1		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/01/07 15 55
-	20		USPAT;	2002/01/07 16:27
		(recess\$3 or indent\$5 or gap) and	US-PGPUB; EPO; JPO;	
		257/\$6.ccls.	DERWENT;	
			IBM TDB	
_	209	(("257/653").CCLS.) or (("257/654").CCLS.)	JPO;	2002/01/07 16:30
		, , , , , , , , , , , , , , , , , , , ,	DERWENT;	
	1		IBM_TDB	0000/01/07 16 00
-	209		JPO	2002/01/07 16:30
-	22		JPO	2002/01/07 16:33
	1.	(("257/654").CCLS.)) and buried		1

	1	((("257/653").CCLS.) or	JPO	2002/01/07 16:33
	_	(("257/654").CCLS.)) and buried and (slit	,	
-	27	or gap or opening) ((("257/213").CCLS.) or	USPAT;	2002/01/07 17:12
		(("257/288").CCLS.) or (("257/327").CCLS.)	US-PGPUB; EPO; JPO;	
		or (("257/335").CCLS.) or (("257/339").CCLS.) or	DERWENT;	
		("257/355") CCLS.)) and (buried adj2	IBM_TDB	
		(region or layer) same (gap or opening or		
_	16	slit)) ((("257/213").CCLS.) or	USPAT;	2002/01/07 17:12
		(("257/288").CCLS.) or (("257/327").CCLS.)	US-PGPUB; EPO; JPO;	
		or (("257/335").CCLS.) or (("257/339").CCLS.) or	DERWENT;	
		(("257/355").CCLS.)) and (buried same	IBM_TDB	
	21	thickness same increase) ((("257/653").CCLS.) or	USPAT;	2002/01/07 17:20
_	21	(("257/654").CCLS.)) and (buried same	US-PGPUB;	1
		thickness)	EPO; JPO; DERWENT;	:
			IBM_TDB	
_	5	((("257/653").CCLS.) or	USPAT; US-PGPUB;	2002/01/07 17:22
		(("257/654").CCLS.)) and (buried same thickness same (greater or increase\$1))	EPO; JPO;	
		Chickness same (greater of interest,	DERWENT;	
		scosso by and (thicked game buried)	IBM_TDB USPAT;	2002/01/07 17:22
-	0	5629558.PN. and (thick\$4 same buried)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	1	5629558.PN. and thick\$4	USPAT;	2002/01/07 17:22
			US-PGPUB; EPO; JPO;	
			DERWENT;	
		(UNOF7/000H) CCLC	IBM_TDB USPAT;	2002/01/07 18:50
_	3222	(("257/213").CCLS.) or (("257/288").CCLS.) or (("257/327").CCLS.) or	US-PGPUB;	2002/01/0/ 1010
		(("257/335").CCLS.) or (("257/339").CCLS.)	EPO; JPO;	
		or (("257/355").CCLS.)	DERWENT; IBM TDB	
_	2	6175143.pn.	USPĀT;	2002/01/07 18:52
		_	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/01/07 19:45
-	2	6177712.pn.	USPAT; US-PGPUB;	2002/01/07 13:43
			EPO; JPO;	
			DERWENT; IBM TDB	
	15	(lateral adj2 field adj effect and	USPAT;	2002/01/07 20:35
_	13	switching).ti,ab.	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	0000 /01 /07 00 20
-	5	(("5629558") or ("5940700") or ("5874767")	USPAT	2002/01/07 20:36
_	398	or ("4485392") or ("6127695")).PN. (257/213).CCLS.	USPAT;	2002/06/02 18:34
_	390		US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM_TDB	1 2002/06/02 19:35
-	733	(257/288).CCLS.	USPAT; US-PGPUB;	2002/06/02 18:35
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

			USPAT;	2002/06/02 18:35
[-	362	(257/327).CCLS.	US-PGPUB;	2002/06/02 18.33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/06/02 19:35
-	456	(257/339).CCLS.	USPAT; US-PGPUB;	2002/06/02 18:35
			EPO; JPO;	'
			DERWENT;	
			IBM_TDB	:
-	1054	(257/355).CCLS.	USPAT;	2002/06/02 18:36
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	154	((("257/213").CCLS.) or	USPĀT;	2002/06/03 08:42
		(("257/288").CCLS.) or (("257/327").CCLS.)	US-PGPUB;	
		or (("257/335").CCLS.) or	EPO; JPO;	
		(("257/339").CCLS.) or (("257/355").CCLS.)) and buried.clm.	DERWENT; IBM TDB	
_	71	(("257/213").CCLS.)) and buffed.cim.	USPAT;	2002/06/02 19:16
	/ -	(("257/288").CCLS.) or (("257/327").CCLS.)	US-PGPUB;	
		or (("257/335").CCLS.) or	EPO; JPO;	
		(("257/339").CCLS.) or	DERWENT;	
		(("257/355").CCLS.)) and buried.clm. and	IBM_TDB	
	4	switch\$3 ((("257/213").CCLS.) or	USPAT;	2002/06/02 19:37
_	4	(("257/213").CCLS.) or (("257/327").CCLS.)	US-PGPUB;	
		or (("257/335").CCLS.) or	EPO; JPO;	
		(("257/339").CCLS.) or	DERWENT;	!
		(("257/355").CCLS.)) and buried.clm. and	IBM_TDB	:
		(gate near4 connect\$3 near4 buried)	USPAT;	2002/06/02 19:43
_	/	((("257/213").CCLS.) or (("257/288").CCLS.) or (("257/327").CCLS.)	US-PGPUB;	2002/00/02 13:13
		or (("257/335").CCLS.) or	EPO; JPO;	
		(("257/339").CCLS.) or	DERWENT;	
		(("257/355").CCLS.)) and buried adj	IBM_TDB	
		contact near3 gate	HCDATT.	2002/06/02 19:45
-	1	dtmos and buried adj contact	USPAT; US-PGPUB;	2002/00/02 19.45
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5	dtmos and buried near3 gate	USPAT;	2002/06/02 19:47
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	0	advantage and dtmos and buried near3 gate	DERWENT	2002/06/02 19:48
-	470	advantage and buried near12 gate	DERWENT	2002/06/02 19:48
-	86	-	DERWENT	2002/06/02 19:48
	60	gate advantage and buried adj contact near6	DERWENT	2002/06/02 20:08
	68	gate	221111111	
-	0		DERWENT	2002/06/02 20:09
		near12 gate and dtmos		0000/05/00 00 50
-	0		DERWENT	2002/06/02 20:10
	1	near12 gate and 257/\$6.ccls.	DERWENT	2002/06/02 20:12
_	195	(buried or body) adj (contact or bias) near12 gate	DETARM	2002/00/02 20:12
_	939		USPAT;	2002/06/02 20:40
		near12 gate	DERWENT	
-	0	(buried or body) adj (contact or bias)	USPAT;	2002/06/02 20:27
		near12 gate and 5348714.pn.	DERWENT	2002/06/02 20:27
-	2		USPAT; DERWENT	2002/00/02 20:2/
	116	near12 gate and 6348714.pn. (buried or body) adj (contact or bias)	USPAT;	2002/06/02 20:40
_	410	near3 gate	DERWENT	
_	69	(buried or body) adj (contact or bias)	USPAT;	2002/06/02 21:16
		near3 connect\$3 near3 gate	DERWENT	

		(buried) adj (contact or bias) near3	USPAT;	2002/06/02 20:43
	56	connect\$3 near3 gate	DERWENT	
		("5895939").PN.	USPAT;	2002/06/02 21:27
	3	("5895939).FM.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	0	parasitic adj capacitance near12 buried	USPAT;	2002/06/02 21:29
į	U	adj contact near12 (vertical adj field adj	US-PGPUB;	
Ì		effect or v-fet or v-igbt)	EPO; JPO;	}
		ellect of v ros says	DERWENT;	
			IBM_TDB	2000 100 100 01 - 14
	1	parasitic adj capacitance near12 (vertical	USPAT;	2002/06/02 21:44
		adj field adj effect or v-fet or v-igbt)	US-PGPUB;	
		adj licia adj bili	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/06/02 22:26
	134	t-gate.ti,ab.	USPAT;	1 2002/00/02 22:26
			US-PGPUB;	•
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/06/02 21:45
	0	t-gate.ti,ab. and buried near4 contact	USPAT;	2002/00/02 21:4.
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/06/02 21:4
_	0	t-gate.ti,ab. and buried near6 contact	USPAT;	2002/06/02 21:4
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/06/02 22:2
-	0	vertical adj DMOSFET near10 "in series"	USPAT; US-PGPUB;	2002/00/02 22:2
			EPO; JPO;	
			DERWENT; IBM TDB	
		40 81	USPAT;	2002/06/02 22:2
_	0	vertical adj MOSFET near10 "in series"	US-PGPUB;	
			EPO; JPO;	
	}		DERWENT;	
			IBM TDB	1
		(VMOSFET or vertical adj MOSFET) near10	USPAT;	2002/06/02 22:2
-		(VMOSFET or vertical adj MOSFEI) heario	US-PGPUB;	•
	1	"in series"	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	.	(FET or transistor) near10 "in series"	USPAT;	2002/06/02 22:4
-]]	(FET OF CLAUSISCOL) Hear to the Series	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
		("6348714").PN.	USPAT;	2002/06/02 22:4
-	4	2 ("6348714").PN.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1	Į.	IBM TDB	1